WHAT IS CLAIMED IS:

1. A dual gate NMOS device, comprising

a drain,

a source,

a first gate between the drain and the source,

a second gate between the drain and the source, wherein the first gate is closer to the drain and the second gate is closer to the source, and

a lightly doped n-type region having a lower doping level than the drain, extending towards the drain from the first gate, wherein the length of the lightly doped region is between 0.18 μm and 0.5μm..

2. A device of claim 1, wherein the lightly doped region extends from the gate edge that lies closest to the drain for the gate that is adjacent the drain.

3. A device of claim 2, wherein the drain includes a drain silicide and a n+ drain ballasting region extending between the drain silicide and the lightly doped region.

4. A device of claim 1, wherein the length of the lightly doped region is between 0.18 μm and 0.25 μm.

5. A device of claim 1, wherein the lightly doped region extends from the drain to the first gate.

6. A method of reducing soft leakage current degradation in a NMOS snapback device that has at least one gate, a n+ drain and a n+ source, comprising

providing for a n-lightly doped region between the gate and the n+ drain of the device, that has a length substantially the same as the n+ drain depth.

7. A method of claim 6, wherein the n-lightly doped region is formed from an NLDD region by masking a region between the gate and the drain during n+ doping of the drain.

8. A method of claim 7, wherein the n-lightly doped region is formed to extend substantially from the edge of the gate for 0.18 μm – 0.5 μm.

9. A method of claim 8, wherein the n-lightly doped region is formed to extend substantially from the edge of the gate for 0.18 μm – 0.25 μm.,

10. A method of claim 7, wherein the mask may comprise a standard mask used in the process such as n+ composite and silicide exclusion mask.

11. A method of claim 1, wherein the NMOS device may be a multiple gate device in which the lightly doped region is located between the drain and the gate nearest the drain.